
2SD1135

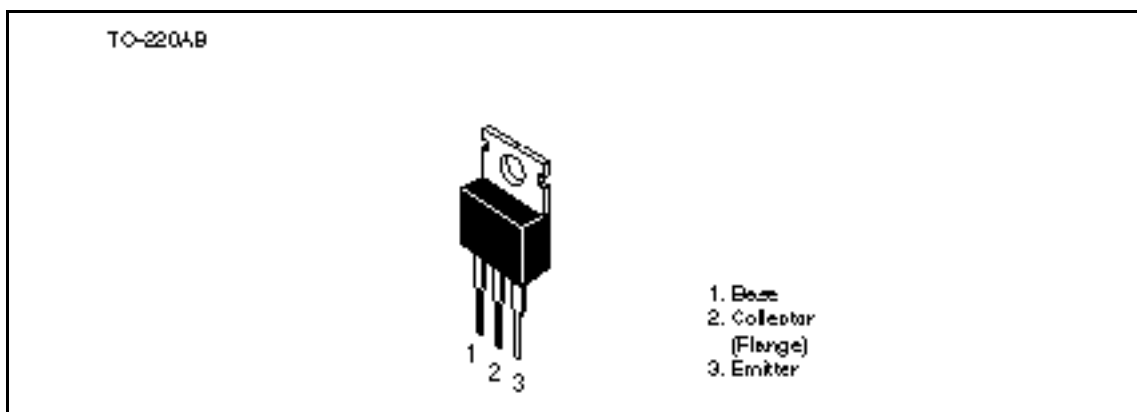
Silicon NPN Triple Diffused

HITACHI

Application

Low frequency power amplifier complementary pair with 2SB859

Outline



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	100	V
Collector to emitter voltage	V_{CEO}	80	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_{C}	4	A
Collector peak current	$I_{\text{C(peak)}}$	8	A
Collector power dissipation	P_{C}^{*1}	40	W
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-45 to +150	$^\circ\text{C}$

Note: 1. Value at $T_{\text{C}} = 25^\circ\text{C}$.

2SD1135

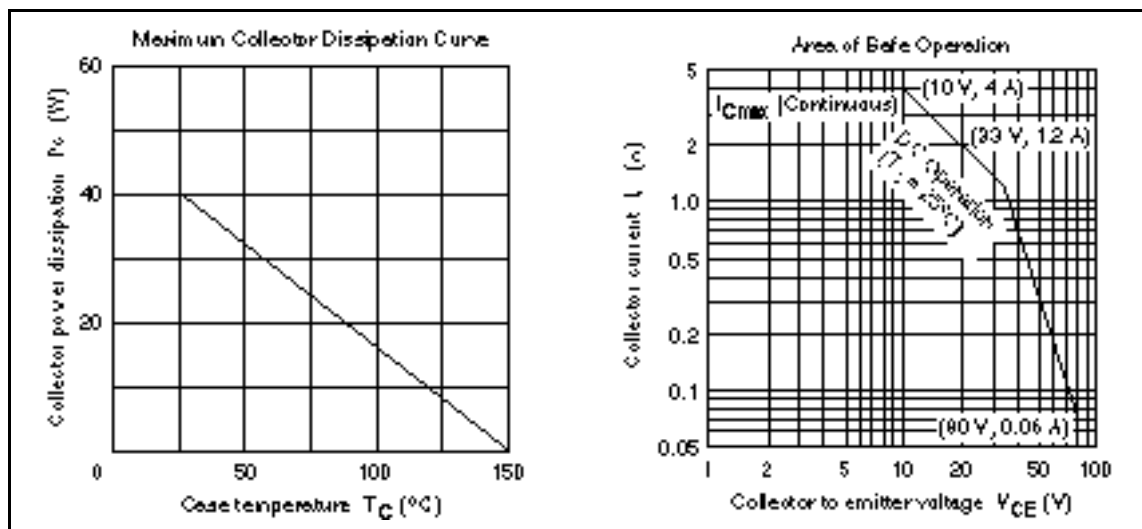
Electrical Characteristics (Ta = 25°C)

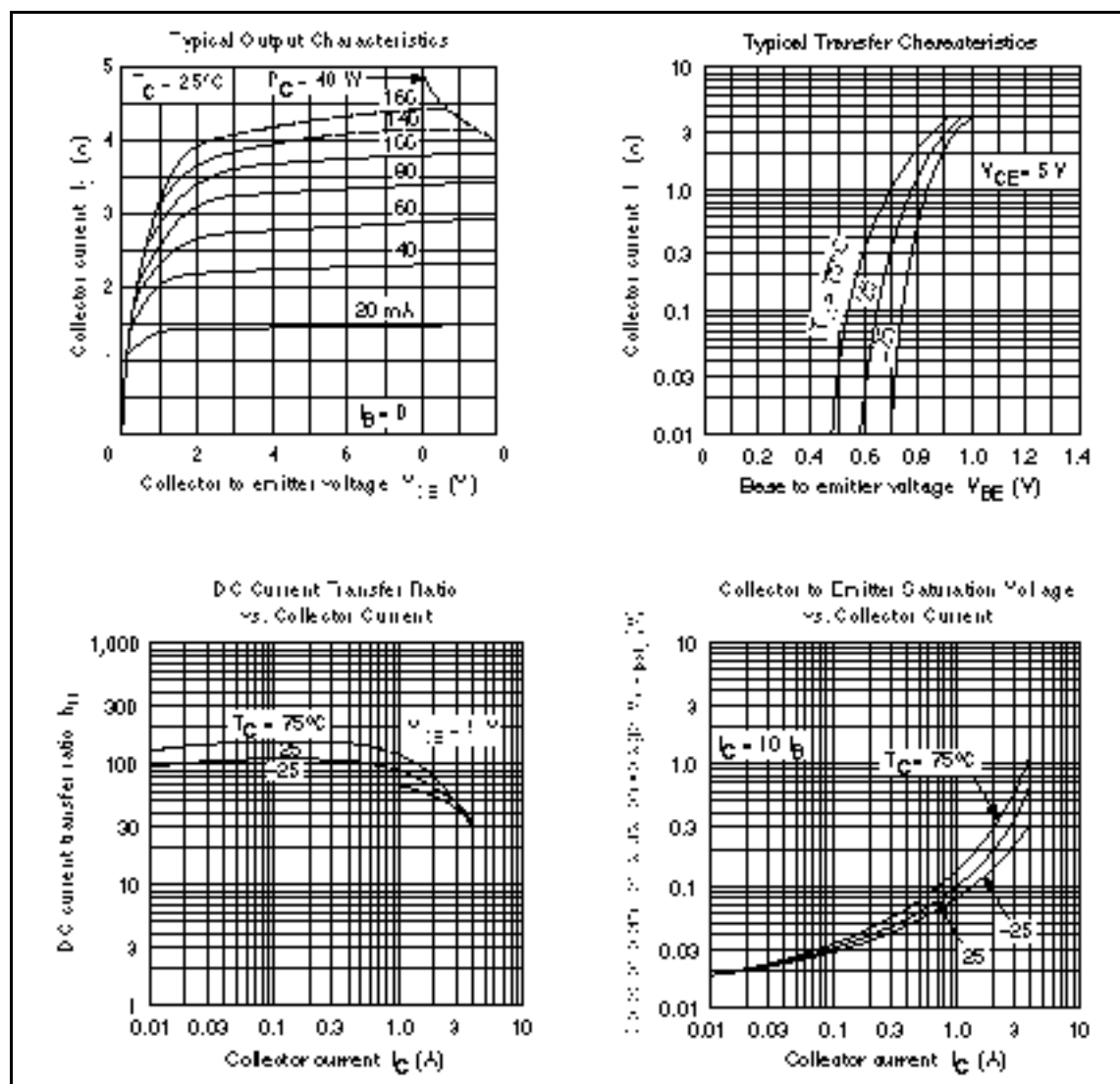
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	80	—	—	V	$I_C = 50 \text{ mA}$, $R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \text{ } \mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.1	mA	$V_{CB} = 80 \text{ V}$, $I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	200		$V_{CE} = 5 \text{ V}$, $I_C = 1 \text{ A}^{*2}$
	h_{FE2}	35	—	—		$V_{CE} = 5 \text{ V}$, $I_C = 0.1 \text{ A}^{*2}$
Base to emitter voltage	V_{BE}	—	—	1.5	V	$V_{CE} = 5 \text{ V}$, $I_C = 1 \text{ A}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	2	V	$I_C = 2 \text{ A}$, $I_B = 0.2 \text{ A}^{*2}$
Gain bandwidth product	f_T	—	10	—	MHz	$V_{CE} = 5 \text{ V}$, $I_C = 0.5 \text{ A}^{*2}$
Collector output capacitance	C_{ob}	—	40	—	pF	$V_{CB} = 20 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$

Notes: 1. The 2SD1135 is grouped by h_{FE1} as follows.

2. Pulse test.

B	C
60 to 120	100 to 200





When using this document, keep the following in mind:

1. This document may, wholly or partially, be subject to change without notice.
2. All rights are reserved: No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without Hitachi's permission.
3. Hitachi will not be held responsible for any damage to the user that may result from accidents or any other reasons during operation of the user's unit according to this document.
4. Circuitry and other examples described herein are meant merely to indicate the characteristics and performance of Hitachi's semiconductor products. Hitachi assumes no responsibility for any intellectual property claims or other problems that may result from applications based on the examples described herein.
5. No license is granted by implication or otherwise under any patents or other rights of any third party or Hitachi, Ltd.
6. **MEDICAL APPLICATIONS:** Hitachi's products are not authorized for use in **MEDICAL APPLICATIONS** without the written consent of the appropriate officer of Hitachi's sales company. Such use includes, but is not limited to, use in life support systems. Buyers of Hitachi's products are requested to notify the relevant Hitachi sales offices when planning to use the products in **MEDICAL APPLICATIONS**.

HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.

Nippon Bldg., 2-6-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan

Tel Tokyo (03) 3270-2111

Fax (03) 3270-5109

For further information write to:

Hitachi America, Ltd.

Semiconductor & IC Div.

2000 Sierra Point Parkway

Brisbane, CA 94005-4835

U.S.A.

Tel 415-589-8300

Fax 415-583-4207

Hitachi Europe GmbH

Electronic Components Group

Continental Europe

Dannebrogstrasse 3

D-85622 Feldkirchen

München

Tel 089-9 91 80-0

Fax 089-9 29 30 00

Hitachi Europe Ltd.

Electronic Components Div.

Northern Europe Headquarters

Whitebrook Park

Lower Cookham Road

High Wycombe

Berkshire SL6 6SYA

United Kingdom

Tel 0628-885000

Fax 0628-778322

Hitachi Asia Pte. Ltd.

45 Collyer Quay #20-00

Hitachi Tower

Singapore 0404

Tel 535-2100

Fax 535-1533

Hitachi Asia (Hong Kong) Ltd.

Unit 705, North Tower,

World Finance Centre

Harbour City, Canton Road

Tsim Sha Tsui, Kowloon

Hong Kong

Tel 27359218

Fax 27308074